

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE

HN1K02FU

HIGH SPEED SWITCHING APPLICATIONS

Unit in mm

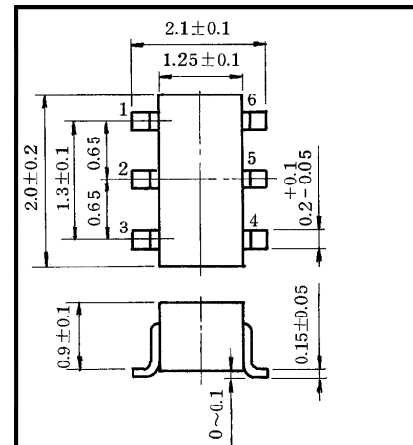
ANALOG SWITCH APPLICATIONS

- 2.5 Volts Gate Drive.
- Low Threshold Voltage : $V_{th}=0.5\sim 1.5V$
- High Speed
- Enhancement-Mode
- Small Package

MAXIMUM RATINGS ($T_a = 25^\circ C$) (Q1, Q2 COMMON)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GSS}	10	V
DC Drain Current	I_D	50	mA
Drain Power Dissipation	P_D^*	200	mW
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55~150	$^\circ C$

* Total Rating



- 1. SOURCE 1 4. SOURCE 2
- 2. GATE 1 5. GATE 2
- 3. DRAIN 2 6. DRAIN 1

US6	
JEDEC	—
EIAJ	—
TOSHIBA	2-2J1C

Weight : 6.8mg

961001EAA2

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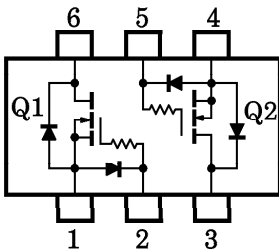
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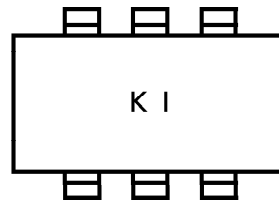
ELECTRICAL CHARACTERISTICS (Ta = 25°C) (Q1, Q2 COMMON)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Gate Leakage Current	I_{GSS}	$V_{GS}=10V, V_{DS}=0$	—	—	1	μA	
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=100\mu A, V_{GS}=0$	20	—	—	V	
Drain Cut-off Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0$	—	—	1	μA	
Gate Threshold Voltage	V_{th}	$V_{DS}=3V, I_D=0.1mA$	0.5	—	1.5	V	
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS}=3V, I_D=10mA$	20	—	—	mS	
Drain-Source ON Resistance	$R_{DS(ON)}$	$I_D=10mA, V_{GS}=2.5V$	—	20	40	Ω	
Input Capacitance	C_{iss}	$V_{DS}=3V, V_{GS}=0, f=1MHz$	—	5.5	—	pF	
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=3V, V_{GS}=0, f=1MHz$	—	1.6	—	pF	
Output Capacitance	C_{oss}	$V_{DS}=3V, V_{GS}=0, f=1MHz$	—	6.5	—	pF	
Switching Time	Turn-on Time	t_{on}	$V_{DD}=3V, I_D=10mA, V_{GS}=0\sim 2.5V$	—	0.14	—	μs
	Turn-off Time	t_{off}	$V_{DD}=3V, I_D=10mA, V_{GS}=0\sim 2.5V$	—	0.14	—	μs

EQUIVALENT CIRCUIT (TOP VIEW)

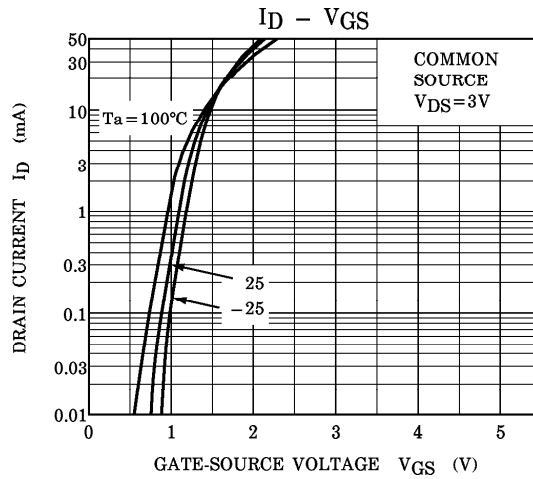
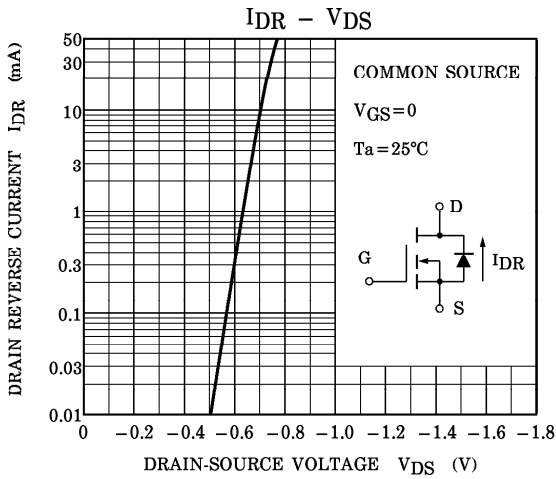
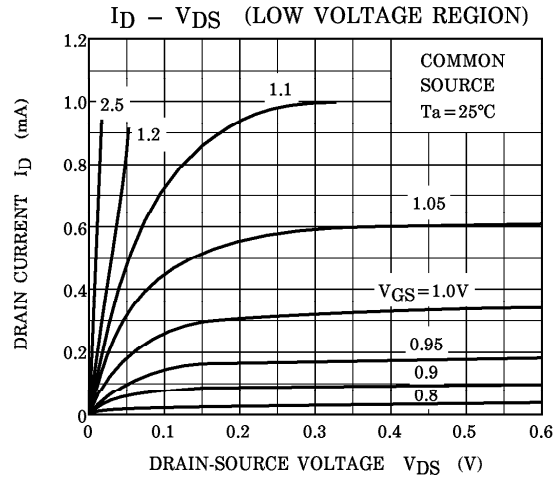
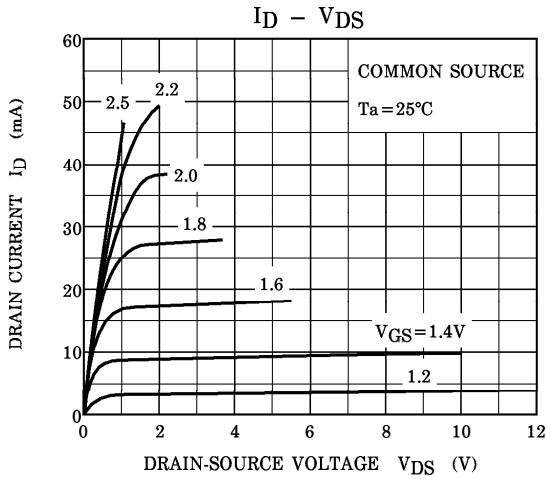
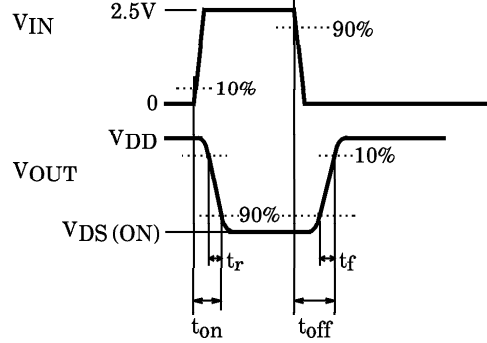
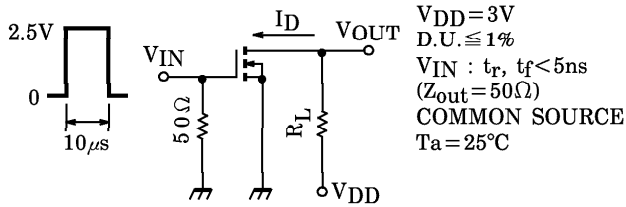


MARKING



(Q1, Q2 COMMON)

SWITCHING TIME TEST CIRCUIT



(Q1, Q2 COMMON)

